

Non-Fermi-liquid transport phenomena in infinite-layer nickelates

Shinichi Hiragami and Seiichiro Onari*

Department of Physics, Nagoya University, Furo-cho, Nagoya 464-8602, Japan.

Recently discovered superconducting infinite-layer nickelates $R\text{NiO}_2$ ($R=\text{Nd, La, Pr}$) attract increasing attention due to the similarities to cuprates. Both $R\text{NiO}_2$ and YBCO cuprates exhibit the non-Fermi-liquid transport behavior, characterized by resistivity proportional to temperature near the quantum critical point of the charge or spin density wave. In this study, we analyze the resistivity of infinite-layer nickelate $\text{Nd}_{0.85}\text{Sr}_{0.15}\text{NiO}_2$ based on a three-dimensional tight-binding model by applying linear response theory. We take account of the self-energy by the fluctuation exchange (FLEX) approximation for the Ni orbital and the T-matrix approximation for an impurity effect on the Nd orbitals. We find that (i) the T -linear resistivity at low temperatures is derived from the spin fluctuations, and (ii) a negative and T -linear Seebeck coefficient is obtained. The resulting T -linear resistivity suggests that NdNiO_2 behaves as a quasi-two-dimensional electron system similar to CeCoIn_5 .

1. Introduction

The superconducting nickelates have recently stimulated much attention due to the similar electronic structures and phase diagrams to cuprates. In particular, the infinite-layer nickelates $R\text{NiO}_2$ ($R=\text{Nd, La, Pr}$) with the superconducting transition temperature $T_c \gtrsim 10\text{K}^{1-4}$ possess a $\text{Ni-}3d^9$ configuration, analogous to the $\text{Cu-}3d^9$ configuration in cuprates. On the other hand, high $T_c \sim 80\text{K}$ has been observed in the double-layer nickelate $\text{La}_3\text{Ni}_2\text{O}_7$ under the pressure.⁵⁾ The double-layer nickelate possesses a $\text{Ni-}3d^{7.5}$ configuration. In these nickelates the superconducting state emerges near the quantum critical point (QCP) of charge density wave (CDW) state, which is also similar to cuprates. However, a significant difference between infinite-layer nickelates and cuprates is the dimensionality of the Fermi surface (FS). The FS in $R\text{NiO}_2$ exhibits three-dimensional (3D) characteristics, in contrast to the two-dimensional (2D) FS in cuprates.

Recently, resonant inelastic X-ray scattering (RIXS) measurements have detected a CDW in $R_{1-x}\text{Sr}_x\text{NiO}_2$.⁶⁻⁹⁾ The 3D structure of the CDW exhibits a period 3 along the x direction and a period 3 to 5 along the z direction, which has been explained by our previous theoretical work based on the paramagnon-interference mechanism.¹⁰⁾ The QCP of the CDW appears at $x \sim 0.15$.⁶⁾ In contrast, very recently, the absence of period 3 along the x direction has been reported.¹¹⁾ Thus, the 3D structure of the CDW has yet to be solved. On the other hand, the spin fluctuations are also developed in $R_{1-x}\text{Sr}_x\text{NiO}_2$, as indicated by a moderate increase in $1/T_1T$ for $T \lesssim 100\text{K}$.¹²⁾

In proximity to the QCP of the spin density wave (SDW) or CDW, non-Fermi-liquid transport phenomena have been observed in both nickelates and cuprates.¹³⁻¹⁹⁾ In $R_{1-x}\text{Sr}_x\text{NiO}_2$ near the QCP of the CDW, the non-Fermi-liquid transport phenomena such as a resistivity $\rho \propto T$ and a T -dependent Hall coefficient has been observed.¹³⁻¹⁵⁾ In triple-layer and quintuple-layer nickelates, a negative and T -linear Seebeck coefficient has been observed.²⁰⁾ The origin of the non-Fermi-liquid transport phenomena in nickelates is an unsolved problem.

Non-Fermi-liquid behaviors of cuprates have been explained by the spin fluctuation theories, such as the self-consistent renormalization (SCR) theory²¹⁻²³⁾ and the fluctuation exchange (FLEX) theory.²⁴⁻²⁶⁾ The spin-fluctuation theories^{23,27)} derive the relation $\rho \propto T$ in 2D systems and $\rho \propto T^{1.5}$ in 3D systems close to the QCP of the SDW. In fact, $\rho \propto T$ has been observed in cuprates,¹⁶⁻¹⁸⁾ which is 2D systems. In addition, Kontani¹⁹⁾ has developed the spin fluctuation theory considering the current vertex corrections, which play important role for the Hall coefficient and the Nernst coefficient in cuprates. We note that the relation $\rho \propto T$ observed in CeCoIn_5 ²⁸⁾ has also been explained by the spin-fluctuation theory.²⁹⁾ Thus, despite CeCoIn_5 has the 3D crystal structure, its electron state is quasi-2D.

In this paper, we study the origin of non-Fermi-liquid T -linear resistivity in infinite-layer nickelate $\text{Nd}_{0.85}\text{Sr}_{0.15}\text{NiO}_2$ based on a 3D tight-binding model. We employ the FLEX approximation for the Ni $d_{x^2-y^2}$ orbital and the T-matrix approximation for an impurity effect on the Nd d_{z^2} and d_{xy} orbitals. The CDW fluctuations are ignored for simplicity in the present study. We find that the T -linear resistivity at low temperatures is induced by the spin fluctuations. Despite the three-dimensional nature of these fluctuations, the T -linear resistivity indicates that this system is quasi-2D. We note that the obtained slope of the resistivity with respect to T is a little smaller than experiments. This slope is expected to increase and approach the experimental value when the CDW fluctuations are taken into account. We also find that the obtained Seebeck coefficient is negative and T -linear, which is consistent with experimental results in triple-layer and quintuple-layer nickelates.²⁰⁾

2. Model and Hamiltonian

Since the non-Fermi-liquid T -linear resistivity has been observed around the hole doping $x = 0.15$ in $\text{Nd}_{1-x}\text{Sr}_x\text{NiO}_2$, we analyze the following 3D three-orbital Hubbard model for $x = 0.15$, where $d_{x^2-y^2}$ orbital of Ni, d_{z^2} and d_{xy} orbitals of Nd are taken into account:

$$H = H^0 + H^U, \quad (1)$$

*onari@s.phys.nagoya-u.ac.jp

where H^0 is the tight-binding model employed on Ref.¹⁰ We introduce the energy shift -0.25eV of Ni $d_{x^2-y^2}$ orbital in order to reproduce the bandstructure with small Fermi pocket of Nd orbitals obtained by the density functional theory (DFT)+DMFT calculation.³⁰ Details of the present model are explained in the Appendix. Figures 1(a) and (b) show band dispersion and 3D FSs in this model. Orbitals 1, 2, and 3 denote Ni $d_{x^2-y^2}$ orbital, Nd d_{z^2} orbital, and Nd d_{xy} orbital, respectively. We stress that an analysis using the 3D model is essential for this system since the FSs have a 3D structure. H_U is the Coulomb interaction, where the Coulomb interaction of only orbital 1 is taken into account since the results including the Coulomb interactions of the three orbitals are almost the same.

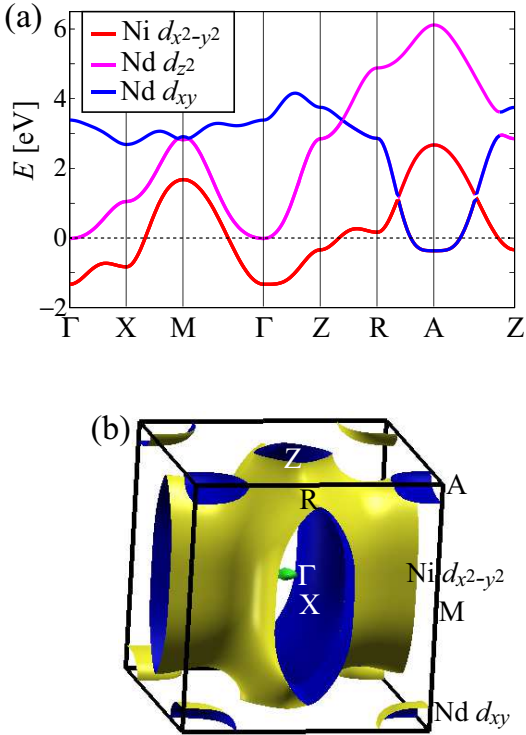


Fig. 1. (a) Bandstructure of the present $\text{Nd}_{0.85}\text{Sr}_{0.15}\text{NiO}_2$ model. Red, purple, and blue lines represent Ni $d_{x^2-y^2}$, Nd d_{z^2} , and Nd d_{xy} orbitals, respectively. (b) 3D FSs in the present model.

3. Formulation

First, we analyze the self-energy of orbital 1 in the FLEX approximation. The self-energy in the FLEX approximation $\hat{\Sigma}^{\text{FLEX}}$ with only $\Sigma_{1,1}^{\text{FLEX}}$ component, the effective interaction for the self-energy in the FLEX approximation V^{FLEX} , the spin (charge) susceptibility $\chi^{s(c)}$, the irreducible susceptibility χ^0 , and Green's function $G_{1,1}$ of orbital 1 are given as

$$\Sigma_{1,1}^{\text{FLEX}}(k) = \frac{T}{N} \sum_q V^{\text{FLEX}}(q) G_{1,1}(k-q) \quad (2)$$

$$V^{\text{FLEX}}(q) = \frac{3}{2} U_1^2 \chi^s(q) + \frac{1}{2} U_1^2 \chi^c(q) - U_1^2 \chi^0(q) \quad (3)$$

$$\chi^{s(c)}(q) = \frac{\chi^0(q)}{1 - (+) U_1 \chi^0(q)} \quad (4)$$

$$\chi^0(q) = -\frac{T}{N} \sum_k G_{1,1}(k+q) G_{1,1}(k) \quad (5)$$

$$G_{1,1}(k) = \left[\frac{1}{(i\epsilon_n - \mu) \hat{1} - \hat{h}^0(\mathbf{k}) - \hat{\Sigma}^{\text{FLEX}}(k)} \right]_{1,1}, \quad (6)$$

where $k = [\mathbf{k}, \epsilon_n = (2n+1)\pi T]$, $q = (\mathbf{q}, \omega_m = 2m\pi T)$. In the present 3D calculation, we employ $N = 64 \times 64 \times 64$ $\mathbf{k}(\mathbf{q})$ meshes and 512 Matsubara frequencies. $\hat{h}^0(\mathbf{k})$ is the matrix expression of H^0 , and μ is the chemical potential. We solve Eqs. (2)-(6) selfconsistently.

Next, we consider the nonmagnetic impurity effect induced by the substitution of Nd and Sr atoms. The impurity effect is taken into account by the T-matrix approximation in the orbital representation;

$$\hat{T}(i\epsilon_n) = [\hat{1} - \hat{I} \hat{G}^{\text{loc}}(i\epsilon_n)]^{-1} \hat{I}, \quad (7)$$

$$\hat{G}^{\text{loc}}(i\epsilon_n) = \frac{1}{N} \sum_k \hat{G}_k(i\epsilon_n), \quad (8)$$

$$\hat{I} = \begin{pmatrix} 0 & 0 & 0 \\ 0 & I_{\text{Nd}} & 0 \\ 0 & 0 & I_{\text{Nd}} \end{pmatrix}, \quad (9)$$

$$\hat{\Sigma}^{\text{imp}} = n_{\text{imp}} \hat{T}(i\epsilon_n), \quad (10)$$

where \hat{G}^{loc} is the local Green's function, \hat{I} is the impurity potential, $\hat{\Sigma}^{\text{imp}}$ is the self-energy induced by the impurity effect on Nd atom, and n_{imp} is the density of impurity. We fix $n_{\text{imp}} = 0.15$ due to the hole doping $x = 0.15$ in the present study. The total self-energy $\hat{\Sigma}_{\text{tot}} = \hat{\Sigma}^{\text{FLEX}} + \hat{\Sigma}^{\text{imp}}$ is given as

$$\hat{\Sigma}_{\text{tot}}(\mathbf{k}, i\epsilon_n) = \begin{pmatrix} \Sigma_{1,1}^{\text{FLEX}}(\mathbf{k}, i\epsilon_n) & 0 & 0 \\ 0 & \Sigma_{2,2}^{\text{imp}}(i\epsilon_n) & 0 \\ 0 & 0 & \Sigma_{3,3}^{\text{imp}}(i\epsilon_n) \end{pmatrix}. \quad (11)$$

To obtain the real frequency dependence, we use the analytic continuation by the Pade approximation,

$$\hat{\Sigma}_{\text{tot}}(\mathbf{k}, i\epsilon_n) \rightarrow \hat{\Sigma}_{\text{tot}}^R(\mathbf{k}, \omega). \quad (12)$$

The transport phenomena are analyzed by using the linear response theory. We calculate the resistivity ρ and the Seebeck coefficient S in the band representation. The conductivity σ_{xx} is given as,

$$\sigma_{xx} = e^2 \sum_{bk} \int \frac{d\omega}{\pi} \left(-\frac{\partial f(\omega)}{\partial \omega} \right) |G_b^R(\mathbf{k}, \omega)|^2 (v_{k,x}^b)^2, \quad (13)$$

where $f(\omega) = [1 + \exp((\omega - \mu)/T)]^{-1}$, and the Green's function in the band representation G_b^R ($b = 1, 2, 3$) is

$$G_b^R(\mathbf{k}, \omega) = \frac{1}{(\omega + \mu) - h_b^0(\mathbf{k}) - \Sigma_{\text{tot}}^b(\mathbf{k}, \omega)}. \quad (14)$$

Here, h_b^0 and Σ_{tot}^b are the band representation of \hat{h}^0 and $\hat{\Sigma}_{\text{tot}}^R$, respectively. $-e$ ($e > 0$) is the electron charge. The velocity is given as $v_{k,x}^b = \frac{\partial h_b^0(\mathbf{k})}{\partial k_x}$, and the resistivity along x -axis is given as,

$$\rho = \frac{1}{\sigma_{xx}}. \quad (15)$$

The Seebeck coefficient S is given by

$$S = -e \frac{L_{xx}}{T \sigma_{xx}}, \quad (16)$$

$$L_{xx} = \sum_{bk} \int \frac{d\omega}{\pi} \left(-\frac{\partial f(\omega)}{\partial \omega} \right) \omega |G_b^R(\mathbf{k}, \omega)|^2 (v_{k,x}^b)^2. \quad (17)$$

In the present study, we set the Coulomb interaction $U_1 = 3\text{eV}$ for orbital 1, which is consistent with the value $U_1 = 3\text{--}4\text{eV}$ obtained by the first-principles calculations.^{31,32)}

4. Results and discussion

First, we present the spin susceptibility for orbital 1 $\chi^s(q)$ in the FLEX approximation. The spin Stoner factor α_s is defined as $\alpha_s = U_1 \max_q \chi^s(q, 0)$. Thus, $\chi^s(q) \propto (1 - \alpha_s)^{-1}$, and $\alpha_s = 1$ corresponds to spin-ordered state.

Figures 2(a) and (b) show the obtained spin susceptibilities for orbital 1 at $T = 10\text{meV}$ on $q_z = 0$ and $q_z = \pi$ planes, respectively. $\chi^s(q, 0)$ has a broad peak around $\mathbf{Q}_s = (\pi, \pi, \pi)$. These results indicate that $\chi^s(q, 0)$ is three-dimensional. As shown in Fig. 2(c), $\alpha_s \sim 0.95$ is obtained at $T = 10\text{meV}$, which corresponds to the moderate spin fluctuations. These moderate spin fluctuations are consistent with the experiment, where $1/T_1 T$ moderately increases for $T \lesssim 100\text{K}$.¹²⁾

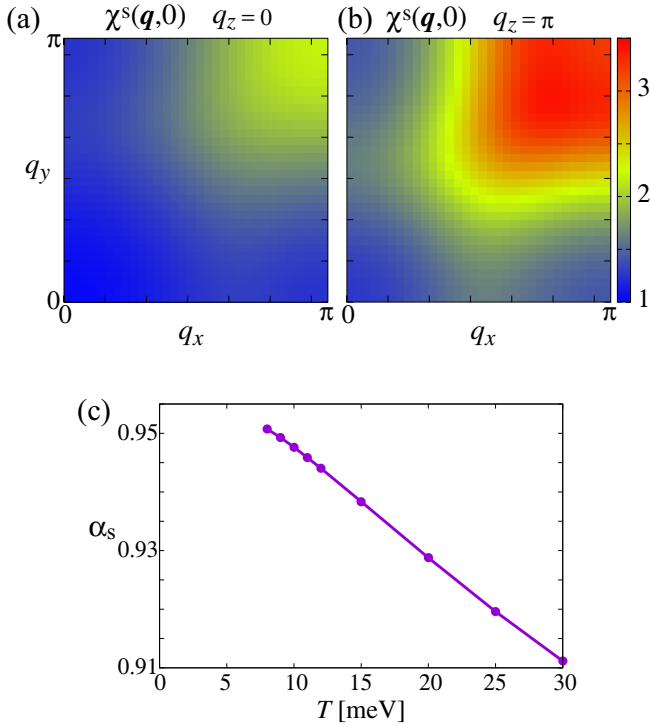


Fig. 2. (a) q dependences of $\chi^s(q, 0)$ given by the FLEX approximation on $q_z = 0$ plane, and (b) that on $q_z = \pi$ plane. (c) T dependence of α_s .

Next, we calculate \mathbf{k} dependence of the mass enhancement factor of orbital 1 $z^{-1}(\mathbf{k})$, which is given as

$$z^{-1}(\mathbf{k}) = \left[1 - \frac{\partial \Sigma_{1,1}^{\text{FLEX}}(\mathbf{k}, \omega)}{\partial \omega} \right]. \quad (18)$$

Figures 3(a) and (b) show obtained $z^{-1}(\mathbf{k})$ on $k_z = 0$ and $k_z = \pi$ planes, respectively. The value of $z^{-1}(\mathbf{k})$ exhibits a k_z dependence, reflecting the three-dimensionality of FS for orbital 1. In addition, the value of $z^{-1}(\mathbf{k})$ on FS in $k_z = 0$ plane is larger than that in $k_z = \pi$ plane.

Hereafter, we analyze the transport phenomena by taking account of the self-energies of both the FLEX approxima-

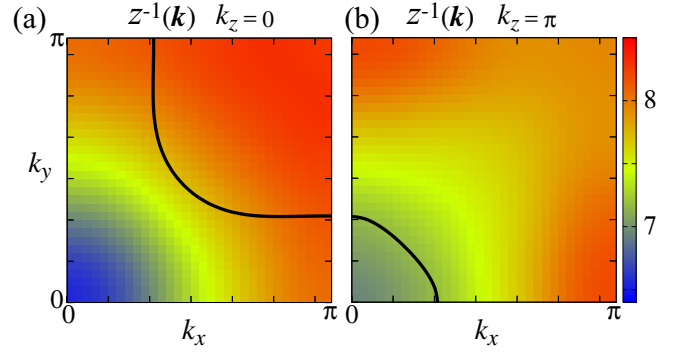


Fig. 3. (a) Obtained \mathbf{k} dependence of mass enhancement factor $z^{-1}(\mathbf{k})$ on $k_z = 0$ plane, and (b) that on $k_z = \pi$ plane. Black line represents the FS.

tion for orbital 1 and the impurity effect for orbitals 2 and 3. Figure 4(a) shows obtained T dependence of resistivity ρ for $I_{\text{Nd}} = 5, 20\text{eV}$, where we use the lattice constant along z -axis $c = 3.267\text{\AA}$. At low temperatures, ρ shows T -linear behavior, which is consistent with the Non-Fermi-liquid behavior observed in experiments.^{13–15)} The obtained slope of the resistivity with respect to T , $7.7 \times 10^{-4}\text{m}\Omega\text{cm/K}$ for $I_{\text{Nd}} = 20\text{eV}$, is close to the experimental value $10.7 \times 10^{-4}\text{m}\Omega\text{cm/K}$ for $x = 0.15$.¹⁵⁾ This slope is expected to increase and approach the experimental value when the CDW fluctuations neglected in this study are taken into account.

To evaluate the three-dimensionality of the present model, we introduce a magnification factor r_z for the inter-layer hopping integrals. $r_z = 1$ and $r_z = 0$ correspond to the original 3D model and a 2D model, respectively. Figure 4(b) shows T dependences of ρ for $r_z = 1, 2, 2.5$ at $I_{\text{Nd}} = 20\text{eV}$. At low temperatures, $\rho \propto T^{0.84}$ for $r_z = 1$, $\rho \propto T^{1.11}$ for $r_z = 2$, and $\rho \propto T^{1.42}$ for $r_z = 2.5$ are obtained by the least-squares fittings for $8 \leq T \leq 15\text{meV}$. In the case of $r_z = 2.5$, T dependence of ρ is very close to $\rho \propto T^{1.5}$, which corresponds to the behavior near the QCP of 3D systems according to the SCR theory.^{21–23)} On the other hand, T dependence of ρ for $r_z = 1$ is approximately $\rho \propto T$, which reflects the behavior near the QCP of 2D systems. This fact confirms that the electron state in the present 3D model for $r_z = 1$ is a quasi-2D. These results are similar to CeCoIn₅ that has a 3D crystal structure but exhibits $\rho \propto T$.^{28,29)} Thus, both electron states of RNiO₂ and CeCoIn₅ are expected to be quasi-2D.

Here, we discuss the obtained T dependence of ρ , which is proportional to T at low temperatures, while it is suppressed and saturated at high temperatures. Considering the orbital decomposition of the resistivity, we obtain

$$\rho = \left(\frac{1}{\rho_{\text{Ni}}} + \frac{1}{\rho_{\text{Nd}}} \right)^{-1}. \quad (19)$$

Here, we denote

$$\rho_{\text{Ni}} \propto \text{Im}\Sigma_{\text{Ni}}, \quad \rho_{\text{Nd}} \propto \text{Im}\Sigma_{\text{Nd}}, \quad (20)$$

where Σ_{Ni} and Σ_{Nd} are self-energies of orbital 1 and that of orbital 2(3), respectively. As shown in Fig. 5, $1/\text{Im}\Sigma_{\text{Ni}}$ is dominant over $1/\text{Im}\Sigma_{\text{Nd}}$ at low temperatures since $\text{Im}\Sigma_{\text{Ni}} \propto T$ is induced by the spin fluctuation, and $\text{Im}\Sigma_{\text{Nd}}$ by the impurity effect is independent of T . In contrast, $1/\text{Im}\Sigma_{\text{Nd}}$ is dominant over $1/\text{Im}\Sigma_{\text{Ni}}$ at high temperatures. Thus, T dependence of ρ

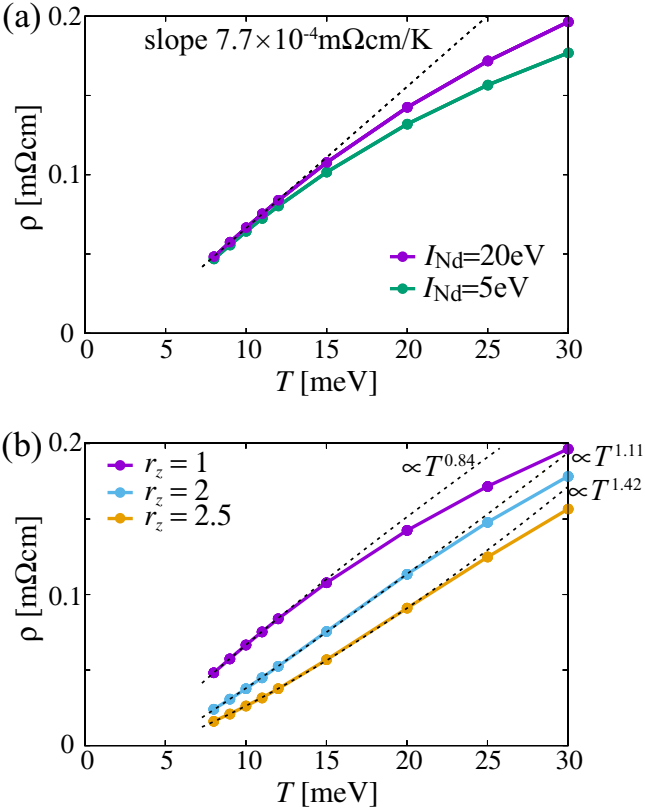


Fig. 4. (a) T dependence of ρ for $I_{\text{Nd}} = 5, 20$ eV. (b) T dependence of ρ for $I_{\text{Nd}} = 20$ eV, with $r_z = 1, 2, 2.5$. Here, r_z represents the magnification factor for the inter-layer hopping integrals. $r_z = 1$ corresponds to the original 3D model.

is $\rho \sim \rho_{\text{Ni}} \propto T$ at low temperatures, and $\rho \sim \rho_{\text{Nd}}$ at high temperatures.

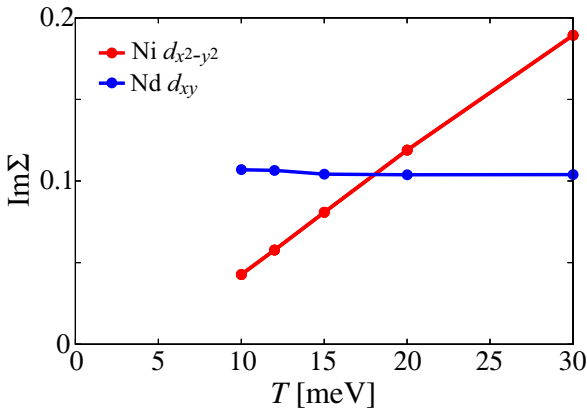


Fig. 5. T dependences of self-energy $\text{Im}\Sigma$ averaged on FS for orbital 1 and 3.

In the following, we examine the doping x dependence of ρ . Low T dependences of ρ at $x = 0.15, 0.3$ are shown in Fig. 5. At $x = 0.3$, $\rho \propto T^{1.90}$ is obtained by the least-squares fittings for $T < 10$ meV, which is consistent with the Fermi-liquid-like behavior observed experimentally as $\rho \sim T^2$ at $x \sim 0.3$.¹⁵⁾ This behavior is due to the reduction of spin fluctuations with increasing hole doping x . In contrast, at $x = 0.15$, T -linear ρ remains for $T \gtrsim 3$ meV, which is also consistent with ex-

perimental results.^{13–15)} However, the obtained T dependence of ρ deviates from linear for $T \lesssim 2$ meV, since the $x = 0.15$ does not correspond to the QCP of the SDW. The temperature range where the T -linear ρ emerges is expected to expand to lower temperatures when the CDW fluctuations are taken into account. Analyzing the effect of CDW fluctuations on resistivity is an important future problem.

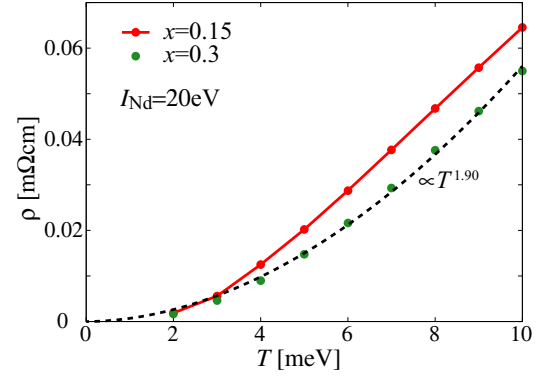


Fig. 6. Low T dependence of ρ for $I_{\text{Nd}} = 20$ eV at $x = 0.15, 0.3$. Dashed line $\rho \propto T^{1.90}$ at $x = 0.3$ is obtained by the least-squares fittings.

Finally, we analyze the Seebeck coefficient S . Figure 6 shows the T dependence of S for $I_{\text{Nd}} = 5, 20$ eV. At low temperatures, T -linear behavior of S is obtained, which is consistent with experimental results.²⁰⁾ The slope $-0.055 \mu\text{V}/\text{K}^2$ for $I_{\text{Nd}} = 20$ eV is very close to the experimental value $-0.050 \mu\text{V}/\text{K}^2$ in triple-layer and quintuple-layer nickelates.²⁰⁾ This behavior of S is similar to that obtained in the model for YBCO cuprates.³³⁾

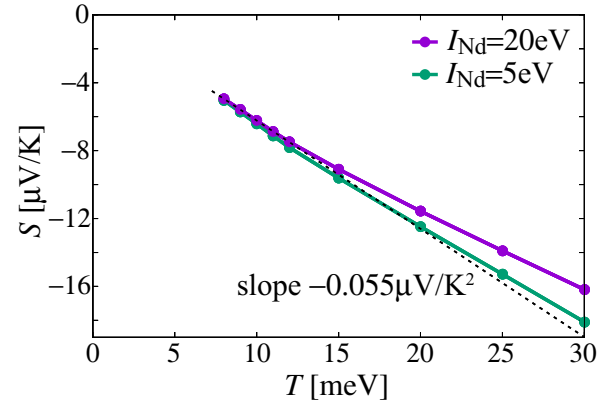


Fig. 7. T dependence of S for $I_{\text{Nd}} = 5, 20$ eV.

5. Conclusion

we studied the origin of non-Fermi-liquid T -linear resistivity in infinite-layer nickelate $\text{Nd}_{0.85}\text{Sr}_{0.15}\text{NiO}_2$ based on a 3D tight-binding model. The self-energy by the FLEX approximation for the Ni orbital and the T-matrix approximation for an impurity effect on the Nd orbitals is taken into account. We found that the T -linear resistivity at low temperatures is induced by the spin fluctuations. Despite the three-dimensional

nature of these fluctuations, the T -linear resistivity indicates that this system is quasi-2D. We note that the obtained slope of the resistivity with respect to T is a little smaller than experiments. This slope is expected to increase and approach the experimental value when the CDW fluctuations neglected in this study are taken into account. We also found that the obtained Seebeck coefficient is negative and T -linear, which is consistent with experiments in triple-layer and quintuple-layer nickelates.

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Appendix: Details of the present model

Here, we explain details of the present model. For Ni $d_{x^2-y^2}$ orbital, we employ the intralayer next-nearest-neighbor hopping t_2 , the intralayer third-nearest one t_3 , interlayer nearest one t_z , and next-nearest-interlayer one t_{z2} to $t_2/t_1 = -1/3$, $t_3/t_1 = 0.2$, $t_z/t_1 = 2/3$, and $t_{z2}/t_1 = -0.165$ ($t_1 = -0.376eV$ is the nearest-neighbor hopping), respectively. In addition, we introduce the energy shift $-0.25eV$ of Ni $d_{x^2-y^2}$ orbital to reproduce the small Fermi pocket of Nd orbitals given by DFT+DMFT calculation.³⁰⁾ The hole-doping x is introduced by the rigid-band shift for all three bands.

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